

1. Scope :

This specification applies to P/N silicon zener diode chips,
Device NO. SD-10814G

2. Structure :

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :
 - Top side : Gold Pad.
 - Back side : Gold Layer.

3. Size :

- 3-1. Chip size : $195 \pm 20 \mu\text{m} \times 195 \pm 20 \mu\text{m}$ ($7.8 \pm 0.8 \text{ mils} \times 7.8 \pm 0.8 \text{ mils}$).
- 3-2. Chip thickness : $150 \pm 20 \mu\text{m}$ ($6.0 \pm 0.8 \text{ mils}$).
- 3-3. Bonding pad : $\phi 125 \pm 10 \mu\text{m}$ ($\phi 5.0 \pm 0.4 \text{ mils}$).
- 3-4. Pattern drawing : Refer to the attached drawing.
- 3-5. Fiducial mark does not apply any characteristics or any incoming inspection.

4. Electrical characteristics (Ta = 25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I_R	$V_R=5V$ $E_e=0\text{mW}/\text{cm}^2$			500	nA
Zener Voltage	V_Z	$I_Z=5\text{mA}$ $E_e=0\text{mW}/\text{cm}^2$	12		16	V
Forward Voltage	V_F	$I_F=10\text{mA}$ $E_e=0\text{mW}/\text{cm}^2$	800		1200	mV

